

2N5303 Transistors

Si NPN Power BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 80

$V_{(BR)CBO}$ (V) 80

I_C Max. (A) 20

Absolute Max. Power Diss. (W) 200

Maximum Operating Temp (θC) 175 \circ

I_{CBO} Max. (A) 1.0m

@ V_{CBO} (V) (Test Condition)

V_{CEsat} Max. (V)

@ I_C (A) (Test Condition)

@ I_B (A) (Test Condition)

h_{FE} Min. Current gain. 15

h_{FE} Max. Current gain. 60

@ I_C (A) (Test Condition) 15

@ V_{CE} (V) (Test Condition) 2.0

f_T Min. (Hz) Transition Freq 2.0M

@ I_C (A) (Test Condition)

@ V_{CE} (V) (Test Condition)

t_d Max. (s) Delay time.

t_r Max. (s) Rise time 1.0u

t_{on} Max. (s) On time.